

UCC27532-Q1 2.5A 和 5A、35V_{MAX} VDD FET 和 IGBT 单栅极驱动器

1 特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 标准的下列特性：
 - 器件温度 1 级
- 低成本栅极驱动器（为驱动 FET 和 IGBT 提供理想解决方案）
- 分立式晶体管对驱动器的出色替代产品（提供与控制器的简便对接）
- CMOS 兼容输入逻辑阈值（在 VDD 大于 18V 时变为固定值）
- 分离输出可实现独立接通和关闭调节
- 通过固定 TTL 兼容型阈值启用
- 在 18V VDD 下具有 2.5A 的高峰值驱动拉电流和 5A 的峰值驱动灌电流
- 从 10V 到高达 35V 的宽 VDD 范围
- 输入引脚可承受低于接地电压且高达 -5V 的直流电压
- 当输入悬空时或在 VDD UVLO 期间，输出保持低电平
- 短暂传播延迟（典型值为 17ns）
- 快速上升和下降时间
（1800pF 负载时的典型值分别为 15ns 和 7ns）
- 欠压锁定（UVLO）
- 用作高侧或低侧驱动器（如果采用适当的偏置和信号隔离设计）
- 低成本、节省空间的 6 引脚 DBV (SOT-23) 封装
- 工作温度范围为 -40°C 至 140°C

2 应用

- 汽车
- 开关模式电源
- 直流/直流转换器
- 光伏逆变器、电机控制、UPS
- 混合动力汽车和电动汽车充电器
- 家用电器
- 可再生能源电源转换
- SiC FET 转换器

3 说明

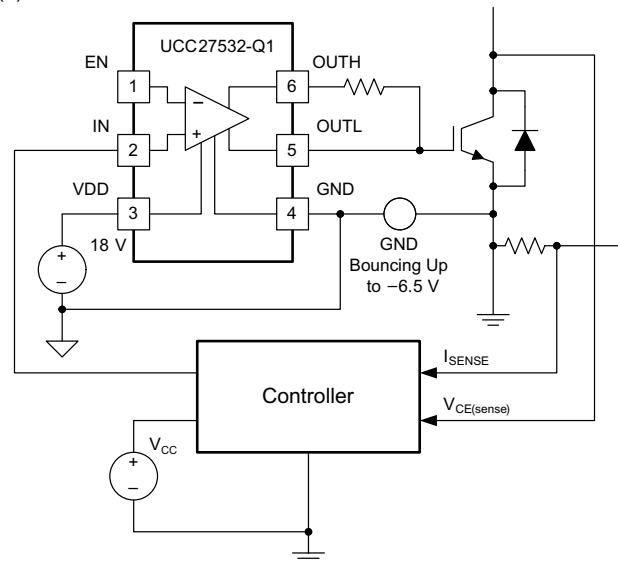
UCC27532-Q1 器件是一款单通道、高速、栅极驱动器，此驱动器可借助于高达 2.5A 拉电流和 5A 灌电流（非对称驱动）峰值电流来有效驱动金属氧化物半导体场效应晶体管 (MOSFET) 和 IGBT 电源开关。非对称驱动中的强劲灌电流能力提升了抗寄生米勒开通效应的能力。UCC27532-Q1 器件还特有一个分离输出配置，在此配置中栅极驱动电流从 OUTH 引脚拉出并从 OUTL 引脚被灌入。这个引脚安排使得用户能够分别在 OUTH 和 OUTL 引脚采用独立的接通和关闭电阻器，并且能很轻易地控制开关的转换率。

此驱动器具有轨到轨驱动功能以及 17ns（典型值）的极小传播延迟。

封装信息

器件型号	封装 ⁽¹⁾	本体尺寸 (标称值)
UCC27532-Q1	DBV (SOT-23, 6)	2.90mm × 1.60mm

(1) 有关所有可用封装，请参阅节 13。



无需负偏压即可驱动 IGBT



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4 说明 (续)

UCC27532-Q1 器件具有 CMOS 输入阈值，此阈值在 VDD 低于或等于 18V 时介于比 VDD 高 55% 的电压值与比 VDD 低 45% 的电压值范围内。当 VDD 高于 18V 时，输入阈值保持在最大水平上。

此驱动器具有一个 EN 引脚，此引脚有一个固定的 TTL 兼容阈值。EN 被内部上拉；将 EN 下拉为低电平禁用驱动器，而将其保持打开可提供正常运行。EN 引脚可被用作一个额外输入，其性能与 IN 引脚一样。

将驱动器的输入引脚保持开状态将把输出保持为低电平。驱动器的逻辑行为如[时序图](#)、[输入/输出逻辑真值表](#)和[节 8.2](#) 所示。

VDD 引脚上的内部电路提供一个欠压闭锁功能，此功能在 VDD 电源电压处于运行范围内之前将输出保持为低电平。

UCC27532-Q1 驱动器采用 6 引脚标准 SOT-23 (DBV) 封装。此器件在 -40°C 至 140°C 的宽运行温度范围内运行。

5 Pin Configuration and Functions

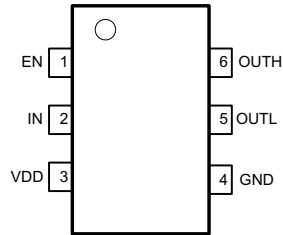


图 5-1. DBV Package 6-Pin SOT-23 Top View

表 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN	1	I	Enable (Pull EN to GND to disable output, pull it high or leave it open to enable the output)
GND	4	—	Ground (all signals are referenced to this node)
IN	2	I	Driver noninverting input (CMOS threshold)
OUTL	5	O	5-A sink current output of driver
OUTH	6	O	2.5-A source current output of driver
VDD	3	I	Bias supply input

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)^{(1) (2) (3)}

		MIN	MAX	UNIT	
Supply voltage range	VDD	- 0.3	35	V	
	Continuous	OUTH, OUTL	- 0.3		VDD +0.3
		IN, EN	- 2		VDD +0.3
	Pulse	OUTH, OUTL (200 ns)	- 5	27	V
IN, EN (1.5 μ s)		- 6.5	27		
Operating virtual junction temperature range, T _J		- 40	150	°C	
Lead temperature	Soldering, 10 seconds		300		
	Reflow		260		
Storage temperature range, T _{stg}		- 65	150		

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to GND unless otherwise noted. Currents are positive into, negative out of the specified terminal. See Packaging Section of the data sheet for thermal limitations and considerations of packages.
- (3) These devices are sensitive to electrostatic discharge; follow proper device handling procedures.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±750	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply voltage range, VDD	10	18	32	V
Operating junction temperature range	- 40		140	°C
Input voltage, IN	- 5		25	V
Enable, EN	- 5		25	

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		UCC27532-Q1	UNIT
		DBV (SOT-23)	
		6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	178.3	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	109.7	°C/W
R _{θJB}	Junction-to-board thermal resistance	28.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	14.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	27.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics

Unless otherwise noted, VDD = 18 V, T_A = T_J = -40°C to 140°C, IN switching from 0 V to VDD, 1-μF capacitor from VDD to GND, f = 100 kHz. Currents are positive into and negative out of the specified terminal. OUTH and OUTL are tied together. Typical condition specifications are at 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BIAS CURRENTS						
I _{DDoff}	Startup current, VDD = 7	IN, EN = VDD	100	240	350	μA
		IN, EN = GND	100	250	350	
UNDERVOLTAGE LOCKOUT (UVLO)						
V _{ON}	Supply start threshold		8	8.9	9.8	V
V _{OFF}	Minimum operating voltage after supply start		7.3	8.2	9.1	V
V _{DD_H}	Supply voltage hysteresis			0.7		V
INPUT (IN)						
V _{IN_H}	Input signal high threshold	VDD = 16V, Output high	8.8	9.4	10	V
V _{IN_L}	Input signal low threshold	VDD = 16V, Output low	6.7	7.3	7.9	V
V _{IN_HYS}	Input signal hysteresis	VDD = 16V		2.1		V
ENABLE (EN)						
V _{EN_H}	Enable signal high threshold	VDD = 16V, Output high	1.7	1.9	2.1	V
V _{EN_L}	Enable signal low threshold	VDD = 16V, Output low	0.8	1	1.2	V
V _{EN_HYS}	Enable signal hysteresis	VDD = 16V		0.9		V
OUTPUTS (OUTH/OUTL)						
I _{SRC/SNK}	Source peak current (OUTH)/ sink peak current (OUTL) ⁽¹⁾	C _{LOAD} = 0.22 μF, f = 1 kHz	- 2.5 / 5			A
V _{OH}	OUTH, high voltage	I _{OUTH} = -10 mA	VDD - 0.2	VDD - 0.12	VDD - 0.07	V
V _{OL}	OUTL, low voltage	I _{OUTL} = 100 mA		0.065	0.125	V
R _{OH}	OUTH, pullup resistance ⁽¹⁾	T _A = 25°C, I _{OUT} = -10 mA	11	12	12.5	Ω
		T _A = -40°C to 140°C, I _{OUT} = -10 mA	7	12	20	
R _{OL}	OUTL, pulldown resistance	T _A = 25°C, I _{OUT} = 100 mA	0.45	0.65	0.85	Ω
		T _A = -40°C to 140°C, I _{OUT} = 100 mA	0.3	0.65	1.25	

(1) Output pullup resistance here is a DC measurement that measures resistance of PMOS structure only, not N-channel structure. The effective dynamic pullup resistance is 3 × R_{OL}.

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _R	Rise time	C _{LOAD} = 1.8 nF		15		ns
t _F	Fall time	C _{LOAD} = 1.8 nF		7		ns
t _{D1}	Turnon propagation delay	C _{LOAD} = 1.8 nF, IN = 0 V to VDD		17	26	ns
t _{D2}	Turnoff propagation delay	C _{LOAD} = 1.8 nF, IN = VDD to 0 V		17	26	ns

(1) Ensured by design and tested during characterization. Not production tested.

(2) See [图 6-1](#).

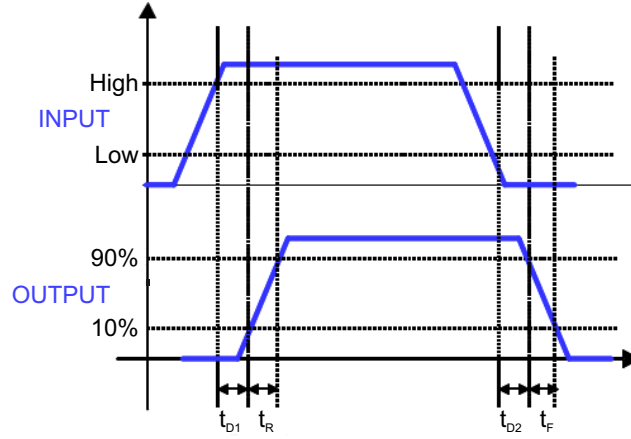


图 6-1. Timing Diagram: (OUTH Tied To OUTL) Input = IN, Output = OUT (EN = VDD) Or Input = EN, Output = OUT (IN = VDD)

6.7 Typical Characteristics

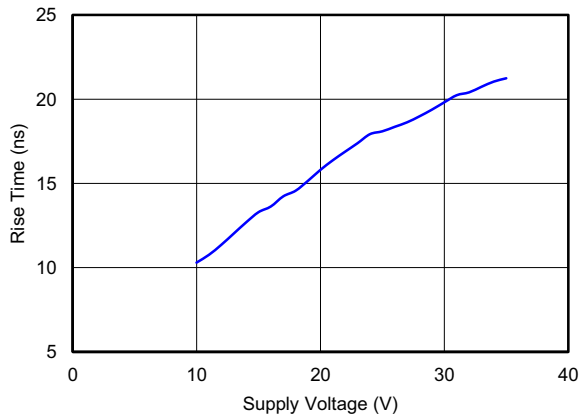


图 6-2. Rise Time vs Supply Voltage

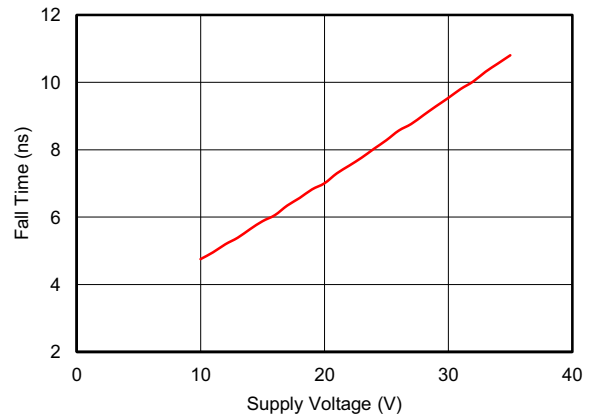


图 6-3. Fall Time vs Supply Voltage

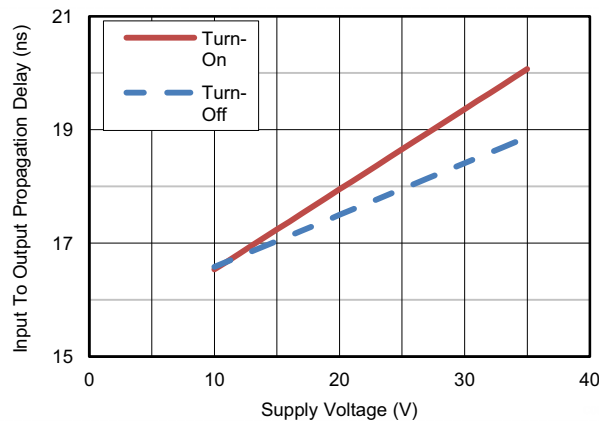


图 6-4. Propagation Delay vs Supply Voltage

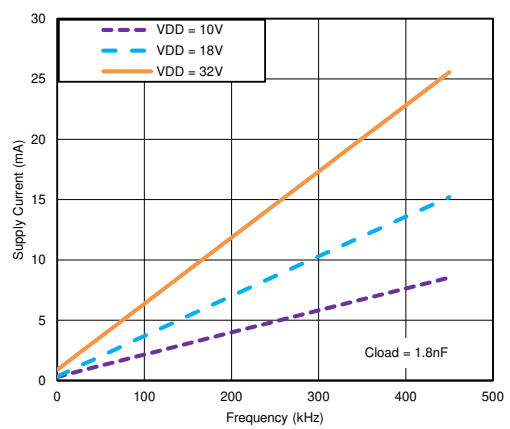


图 6-5. Operating Supply Current vs Frequency

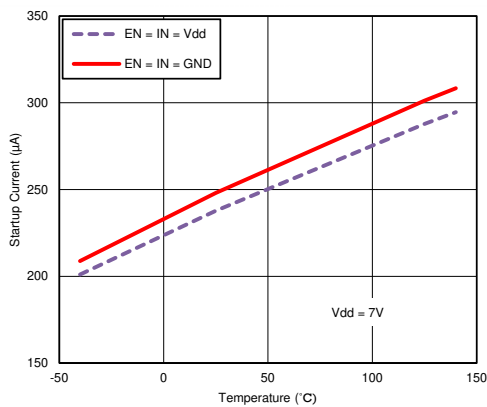


图 6-6. Start-Up Current vs Temperature

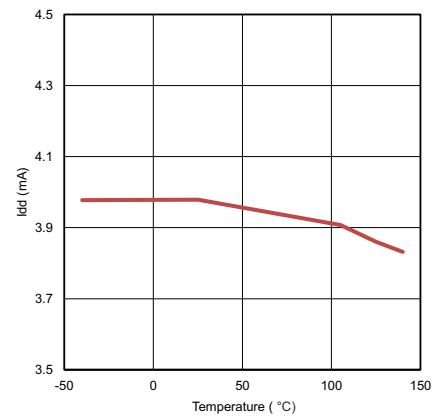


图 6-7. Operating Supply Current vs Temperature (Output Switching)

6.7 Typical Characteristics (continued)

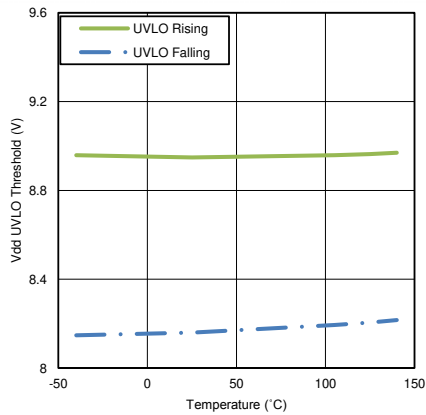


图 6-8. UVLO Threshold Voltage vs Temperature

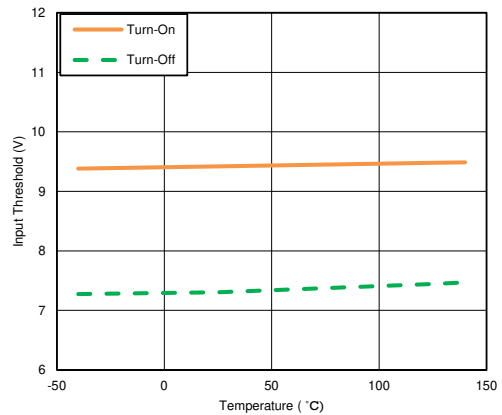


图 6-9. Input Threshold vs Temperature

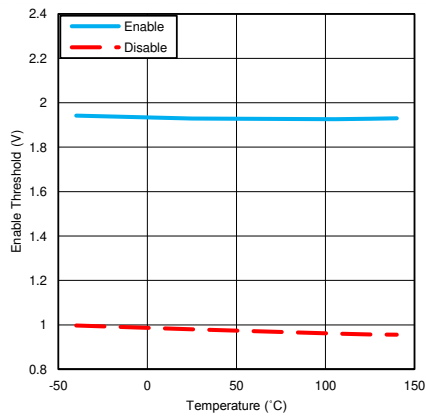


图 6-10. Enable Threshold vs Temperature

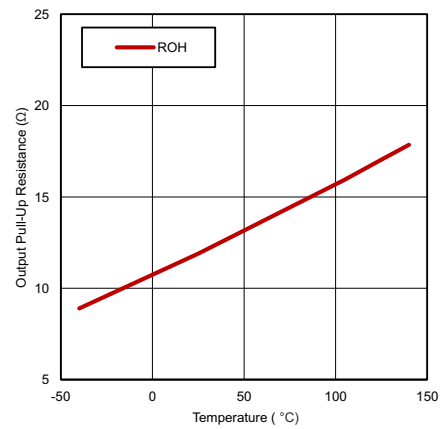


图 6-11. Output Pullup Resistance vs Temperature

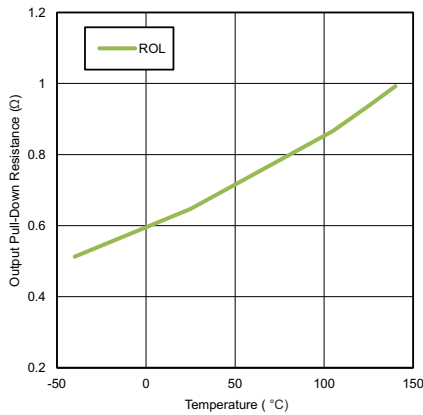


图 6-12. Output Pulldown Resistance vs Temperature

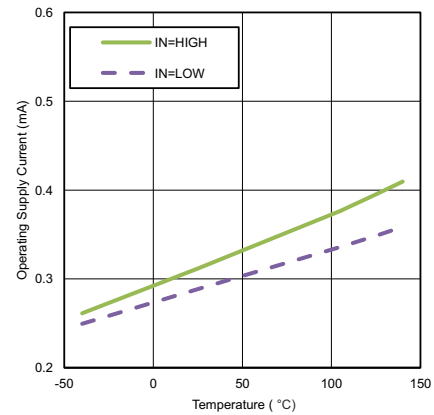


图 6-13. Operating Supply Current vs Temperature (Output in DC ON and OFF Condition)

6.7 Typical Characteristics (continued)

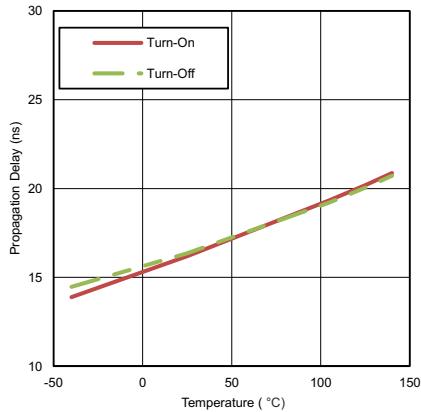


图 6-14. Input-to-Output Propagation Delay vs Temperature

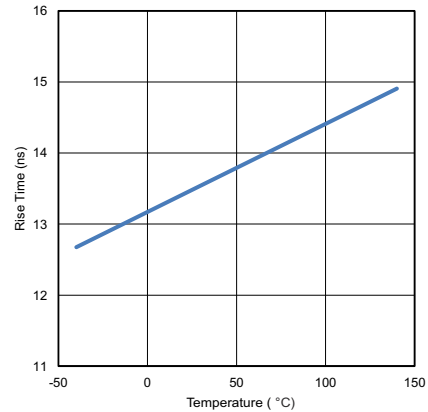


图 6-15. Rise Time vs Temperature

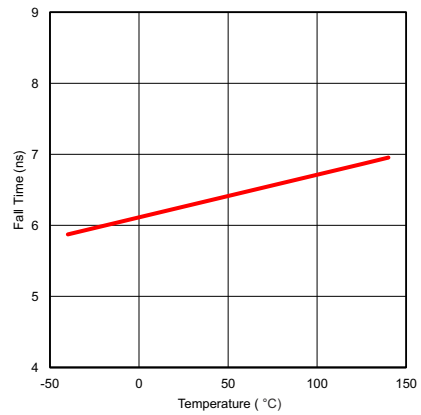


图 6-16. Fall Time vs Temperature

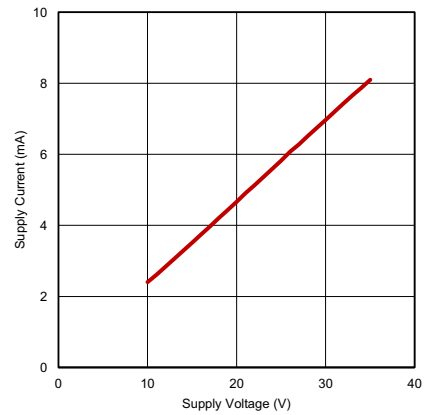


图 6-17. Operating Supply Current vs Supply Voltage (Output Switching)

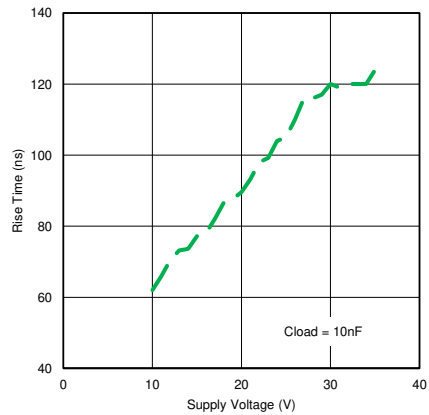


图 6-18. Rise Time vs Supply Voltage

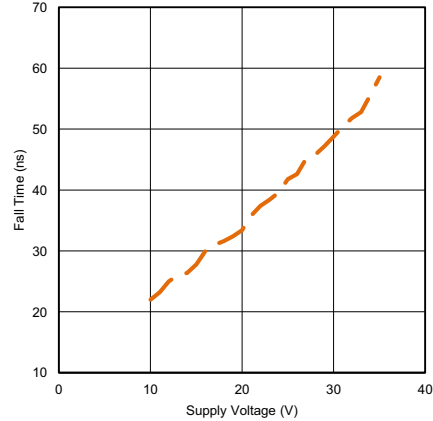


图 6-19. Fall Time vs Supply Voltage

7 Detailed Description

7.1 Overview

High-current gate driver devices are required in switching power applications for a variety of reasons. To enable fast switching of power devices and reduce associated switching power losses, a powerful gate driver can be used between the PWM output of controllers or signal isolation devices and the gates of the power semiconductor devices. Further, gate drivers are indispensable when having the PWM controller directly drive the gates of the switching devices is not feasible. This situation is often encountered because the PWM signal from a digital controller or signal isolation device is often a 3.3-V or 5-V logic signal which is not capable of effectively turning on a power switch. A level shifting circuitry is required to boost the logic-level signal to the gate-drive voltage in order to fully turn on the power device and minimize conduction losses. Traditional buffer drive circuits based on NPN and PNP bipolar (or P-channel and N-channel MOSFET) transistors in totem-pole arrangement, being emitter-follower configurations, prove inadequate for this function because these circuits lack level-shifting capability and low-drive voltage protection. Gate drivers effectively combine both the level-shifting, buffer drive, and UVLO functions. Gate drivers have other uses such as minimizing the effect of switching noise by locating the high-current driver physically close to the power switch, driving gate-drive transformers, controlling floating power device gates, and reducing power dissipation and thermal stress in controllers by moving gate charge power losses into itself.

The UCC27532-Q1 device is very flexible in this role with a strong current-drive capability and wide supply-voltage range up to 35 V. These features allow the driver to be used in 12-V Si MOSFET applications, 20-V and - 5-V (relative to source) SiC FET applications, 15-V and - 15-V (relative to emitter) IGBT applications, and many others. As a single-channel driver, the UCC27532-Q1 device can be used as a low-side or high-side driver. To use the device as a low-side driver, the switch ground is typically the system ground so it can be connected directly to the gate driver. To use as a high-side driver with a floating return node, however, signal isolation is required from the controller as well as an isolated bias to the UCC27532-Q1 device. Alternatively, in a high-side drive configuration the UCC27532-Q1 device can be tied directly to the controller signal and biased with a non-isolated supply. However, in this configuration the outputs of the UCC27532-Q1 device must drive a pulse transformer which then drives the power-switch to work properly with the floating source and emitter of the power switch. Further, having the ability to control turnon and turnoff speeds independently with both the OUTH and OUTL pins ensures optimum efficiency while maintaining system reliability. These requirements coupled with the need for low propagation delays and availability in compact, low-inductance packages with good thermal capability makes gate driver devices such as the UCC27532-Q1 device extremely important components in switching power combining benefits of high-performance, low cost, component count and board-space reduction, and simplified system design.

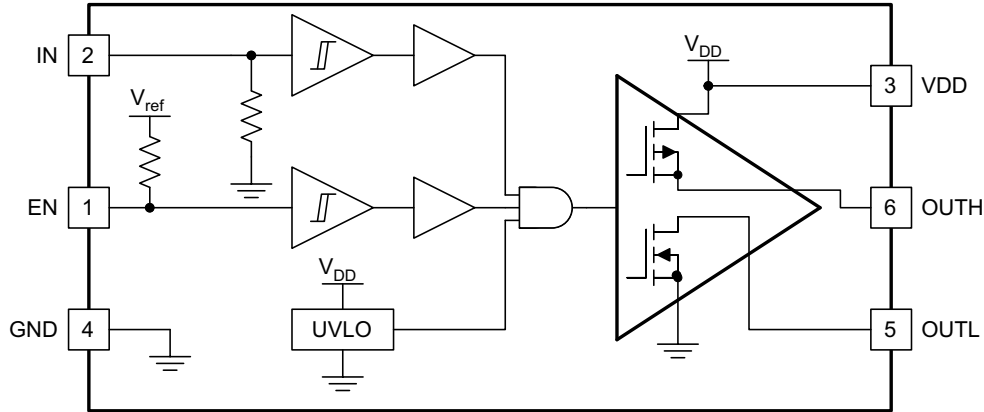
表 7-1. UCC27532-Q1 Features and Benefits

FEATURE	BENEFIT
High source and sink current capability, 2.5 A and 5 A (asymmetrical).	High current capability offers flexibility in employing UCC27532-Q1 device to drive a variety of power switching devices at varying speeds.
Low 17 ns (typ) propagation delay.	Extremely low pulse transmission distortion.
Wide VDD operating range of 10 V to 32 V.	Flexibility in system design.
	Can be used in split-rail systems such as driving IGBTs with both positive and negative (relative to Emitter) supplies.
	Optimal for many SiC FETs.
VDD UVLO protection.	Outputs are held Low in UVLO condition, which ensures predictable, glitch-free operation at power up and power down.
	High UVLO of 8.9 V typical ensures that power switch is not on in high-impedance state which could result in high power dissipation or even failures.
Outputs held low when input pin (IN) in floating condition.	Safety feature, especially useful in passing abnormal condition tests during safety certification
Split output structure (OUTH, OUTL).	Allows independent optimization of turnon and turnoff speeds using series gate resistors.
Strong sink current (5 A) and low pulldown impedance (0.65 Ω).	High immunity to high dV/dt Miller turnon events.
CMOS compatible input threshold logic with wide 2.1-V hysteresis.	Excellent noise immunity.

表 7-1. UCC27532-Q1 Features and Benefits (续)

FEATURE	BENEFIT
Input capable of withstanding - 6.5 V.	Enhanced signal reliability in noisy environments that experience ground bounce on the gate driver.

7.2 Functional Block Diagram



NOTE: EN Pullup Resistance to V_{ref} = 500 k Ω , V_{ref} = 5.8 V, In Pulldown Resistance to GND = 230 k Ω

7.3 Feature Description

7.3.1 VDD Undervoltage Lockout

The UCC27532-Q1 device has an internal undervoltage-lockout (UVLO) protection feature on the VDD-pin supply-circuit blocks. To ensure acceptable power dissipation in the power switch, this UVLO prevents the operation of the gate driver at low supply voltages. Whenever the driver is in UVLO condition (when the VDD voltage less than V_{ON} during power up and when the VDD voltage is less than V_{OFF} during power down), this circuit holds all outputs LOW, regardless of the status of the inputs. The UVLO is typically 8.9 V with a 700-mV typical hysteresis. This hysteresis helps prevent chatter when low-VDD supply voltages have noise from the power supply. This hysteresis also prevents chatter when there are droops in the VDD bias voltage when the system commences switching and there is a sudden increase in I_{DD} . The capability to operate at voltage levels such as 10 V to 32 V provides flexibility to drive Si MOSFETs, IGBTs, and emerging SiC FETs.

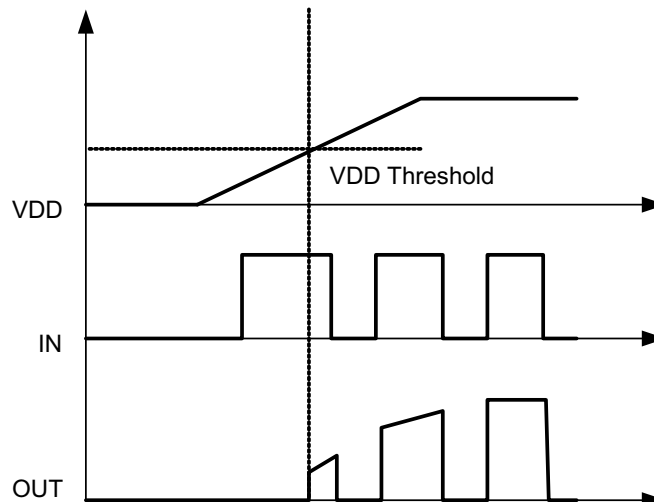


图 7-1. Power Up

7.3.2 Input Stage

The input pin of UCC27532-Q1 device is based on a standard CMOS-compatible input-threshold logic that is dependent on the VDD supply voltage. The input threshold is approximately 55% of VDD for rise and 45% of VDD for fall. With 18-V VDD, the typical high threshold is 9.4 V and the typical low threshold is 7.3 V. The 2.1-V hysteresis offers excellent noise immunity compared to traditional TTL logic implementations where the hysteresis is typically less than 0.5 V. For proper operation using CMOS input, the input signal level must be at a voltage equal to VDD. Using an input signal slightly larger than the threshold but less than VDD for the CMOS input can result in slower propagation delay from input to output (for example). This device also features tight control of the input-pin threshold voltage levels which eases system design considerations and ensures stable operation across temperature. The very low input capacitance, typically 20 pF, on these pins reduces loading and increases switching speed.

The device features an important safety function where the output is held in the low state whenever the input pin is in a floating condition. This function is achieved using GND pulldown resistors on the noninverting input pin (IN pin), as shown in the .

The input stage of the driver is best driven by a signal with a short rise or fall time. Caution must be exercised whenever the driver is used with slowly varying input signals, especially in situations where the device is located in a separate daughter board or PCB layout has long input-connection traces:


- High dI/dt current from the driver output coupled with board layout parasitics can cause ground bounce. Because the device features just one GND pin which can be referenced to the power ground, this can interfere with the differential voltage between input pins and GND and can trigger an unintended change of output state. Because of the fast 17-ns propagation delay, this can ultimately result in high-frequency oscillations, which increases power dissipation and poses a risk of damage
- 2.1-V input threshold hysteresis boosts noise immunity compared to most other industry standard drivers.

If limiting the rise or fall times to the power device to reduce EMI is necessary, then an external resistance is highly recommended between the output of the driver and the power device instead of adding delays on the input signal. This external resistor has the additional benefit of reducing part of the gate-charge-related power dissipation in the gate-driver device package and transferring the dissipation into the external resistor itself.

7.3.3 Enable Function

The enable (EN) pin of the UCC27532-Q1 device has an internal pullup resistor to an internal reference voltage. Therefore, leaving the EN pin floating turns on the driver and allows it to send output signals properly. If desired, the EN pin can also be driven by low-voltage logic to enable and disable the driver.

7.3.4 Output Stage

 7-2 shows the output stage of the UCC27532-Q1 device. The UCC27532-Q1 device features a unique architecture on the output stage which delivers the highest peak-source current when it is most needed during the Miller plateau region of the power switch turnon transition (when the power switch drain or collector voltage experiences dV/dt). The device output stage features a hybrid pullup structure using a parallel arrangement of N-Channel and P-Channel MOSFET devices. By turning on the N-Channel MOSFET during a narrow instant when the output changes state from low to high, the gate driver device is able to deliver a brief boost in the peak sourcing current enabling fast turnon.

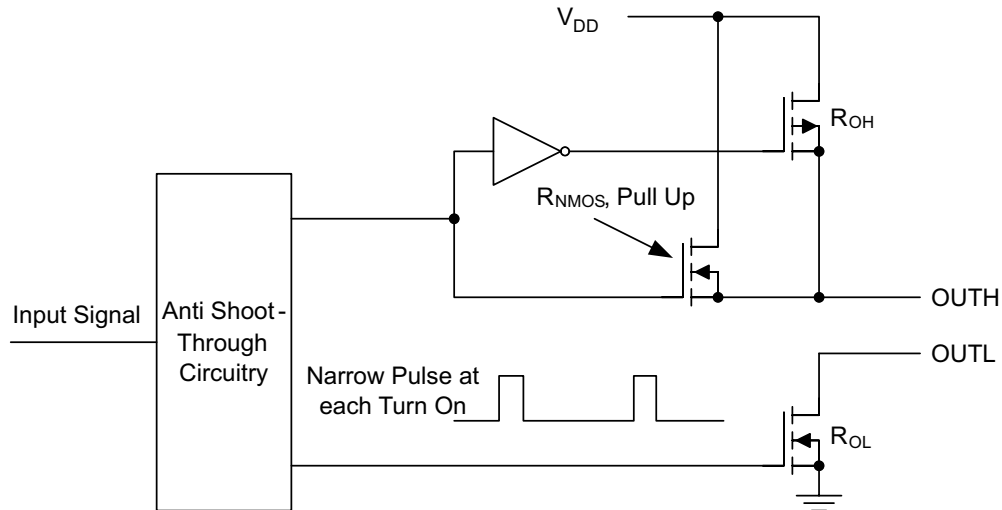


图 7-2. UCC27532-Q1 Gate-Driver Output Stage

The R_{OH} parameter (see 节 6.5) is a DC measurement and is representative of the on-resistance of the P-Channel device only because the N-Channel device is turned-on only during output change of state from low to high. Thus the effective resistance of the hybrid pullup stage is much lower than what is represented by R_{OH} parameter. The pulldown structure is composed of a N-Channel MOSFET only. The R_{OL} parameter (see 节 6.5), which is also a DC measurement, is representative of true impedance of the pulldown stage in the device. In UCC27532-Q1 device, the effective resistance of the hybrid pullup structure is approximately $3 \times R_{OL}$.

The UCC27532-Q1 device is capable of delivering 2.5-A source, 5-A Sink (asymmetrical drive) at $V_{DD} = 18$ V. Strong sink capability in asymmetrical drive results in a very low pulldown impedance in the driver output stage which boosts immunity against the parasitic Miller turnon (high slew-rate dV/dt turnon) effect that is seen in both IGBT and FET power switches.

An example of a situation where Miller turnon is a concern is synchronous rectification (SR). In SR application, the dV/dt occurs on MOSFET drain when the MOSFET is already held in the off state by the gate driver. The current charging the C_{GD} Miller capacitance during this high dV/dt is shunted by the pulldown stage of the driver. If the pulldown impedance is not low enough then a voltage spike can result in the V_{GS} of the MOSFET, which can result in spurious turnon. This phenomenon is illustrated in [图 7-3](#).

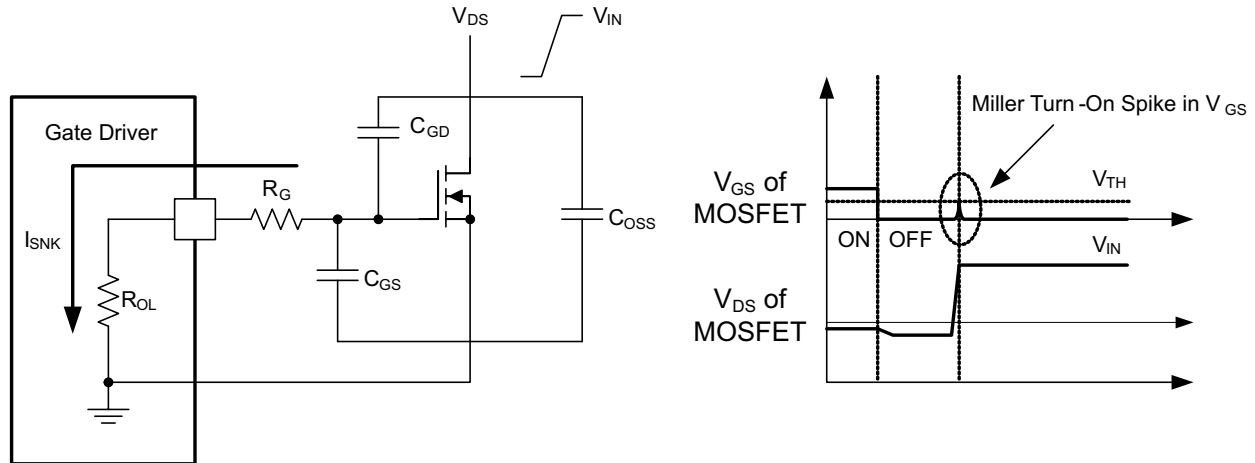


图 7-3. Low Pulldown Impedance in the UCC27532-Q1 Device (Output Stage Mitigates Miller Turnon Effect)

The driver output voltage swings between VDD and GND providing rail-to-rail operation because of the MOS output stage which delivers very low dropout. The presence of the MOSFET body diodes also offers low impedance to switching overshoots and undershoots which means that in many cases, external Schottky diode clamps can be eliminated.

7.4 Device Functional Modes

表 7-2. Input and Output Logic Truth Table

IN PIN	EN PIN	OUTH PIN	OUTL PIN	OUT (OUTH and OUTL pins tied together)
L	L	High-impedance	L	L
L	H	High-impedance	L	L
H	L	High-impedance	L	L
H	H	H	High-impedance	H

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

High-current gate driver devices are required in switching power applications for a variety of reasons. To enable fast switching of power devices and reduce associated switching power losses, a powerful gate driver can be employed between the PWM output of controllers or signal isolation devices and the gates of the power semiconductor devices. Further, gate drivers are indispensable when sometimes it is just not feasible to have the PWM controller directly drive the gates of the switching devices. The situation will be often encountered because the PWM signal from a digital controller or signal isolation device is often a 3.3-V or 5-V logic signal which is not capable of effectively turning on a power switch. A level-shifting circuitry is needed to boost the logic-level signal to the gate-drive voltage to fully turn on the power device and minimize conduction losses. Traditional buffer drive circuits based on NPN/PNP bipolar, (or P- N-channel MOSFET), transistors in totem-pole arrangement, being emitter follower configurations, prove inadequate for this because they lack level-shifting capability and low-drive voltage protection. Gate drivers effectively combine both the level-shifting, buffer drive and UVLO functions. Gate drivers also find other needs such as minimizing the effect of switching noise by locating the high-current driver physically close to the power switch, driving gate-drive transformers and controlling floating power device gates, reducing power dissipation and thermal stress in controllers by moving gate charge power losses into itself.

The UCC27532-Q1 is very flexible in this role with a strong current drive capability and wide supply voltage range up to 32 V. This allows the driver to be used in 12-V Si MOSFET applications, 20-V and -5-V (relative to Source) SiC FET applications, 15-V and -15-V (relative to Emitter) IGBT applications and many others. As a single-channel driver, the UCC27532-Q1 can be used as a low-side or high-side driver. To use as a low-side driver, the switch ground is usually the system ground so it can be connected directly to the gate driver. To use as a high-side driver with a floating return node however, signal isolation is needed from the controller as well as an isolated bias to the UCC27532-Q1. Alternatively, in a high-side drive configuration the UCC27532-Q1 can be tied directly to the controller signal and biased with a nonisolated supply. However, in this configuration the outputs of the UCC27532-Q1 must drive a pulse transformer which then drives the power-switch to work properly with the floating source and emitter of the power switch. Further, having the ability to control turnon and turnoff speeds independently with both the OUTH and OUTL pins ensures optimum efficiency while maintaining system reliability. These requirements coupled with the need for low propagation delays and availability in compact, low-inductance packages with good thermal capability makes gate driver devices such as the UCC27532-Q1 extremely important components in switching power combining benefits of high-performance, low cost, component count and board space reduction and simplified system design.

8.2 Typical Applications

8.2.1 Driving IGBT Without Negative Bias

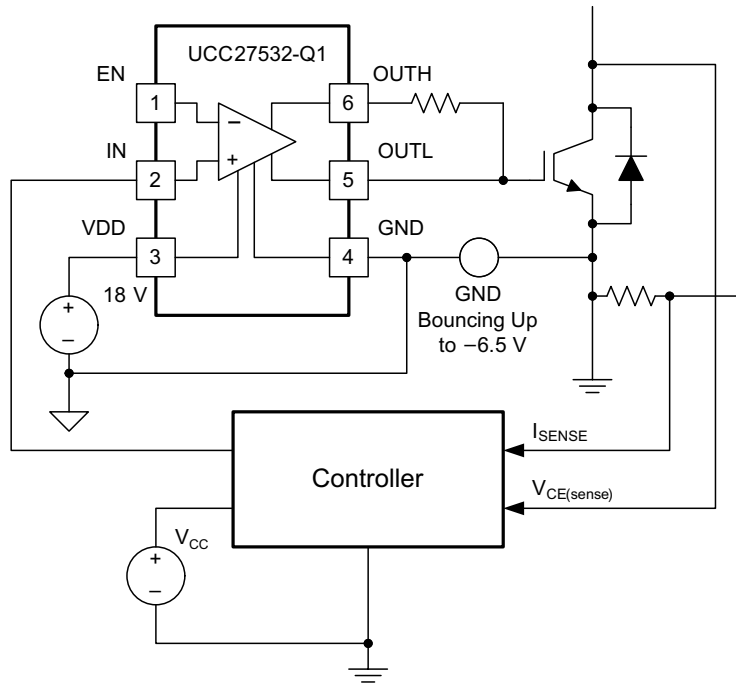


图 8-1. Driving IGBT Without Negative Bias Schematic

8.2.1.1 Design Requirements

When selecting the proper gate driver device for an end application, some design considerations must be evaluated first to make the most appropriate selection. The following design parameters should be used when selecting the proper gate driver device for an end application: input-to-output configuration, the input threshold type, bias supply voltage levels, peak source and sink currents, availability of independent enable and disable functions, propagation delay, power dissipation, and package type. See the example design parameters and requirements in 表 8-1.

表 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
IN-OUT configuration	Noninverting
Input threshold type	CMOS
Bias supply voltage levels	18 V
Negative output low voltage	N/A
$dVDS/dt^{(1)}$	20 V/ns
Enable function	Yes
Disable function	N/A
Propagation delay	<30 ns
Power dissipation	<0.25 W
Package type	DBV

- (1) $dVDS/dt$ is a typical requirement for a given design. This value can be used to find the peak source/sink currents needed as shown in 节 8.2.1.2.4.

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 Input-to-Output Configuration

The design should specify which type of input-to-output configuration should be used. See [表 7-2](#) for UCC27532-Q1 device functionality.

8.2.1.2.2 Input Threshold Type

The type of Input voltage threshold determines the type of controller that can be used with the gate driver device. See the table for the actual input threshold voltage levels and hysteresis specifications for the UCC27532-Q1 devices.

8.2.1.2.3 VDD Bias Supply Voltage

The bias supply voltage to be applied to the VDD pin of the device should never exceed the values listed in the table. However, different power switches demand different voltage levels to be applied at the gate terminals for effective turnon and turnoff. With certain power switches, a positive gate voltage may be required for turnon and a negative gate voltage may be required for turnoff, in which case the VDD bias supply equals the voltage differential. With an operating range from 10 V to 32 V, the UCC27532-Q1 devices can be used to drive a power switches such as power MOSFETS and IGBTs ($V_{GE} = 15\text{ V}, 18\text{ V}$).

8.2.1.2.4 Peak Source and Sink Currents

Generally, the switching speed of the power switch during turnon and turnoff should be as fast as possible to minimize switching power losses. The gate driver device must be able to provide the required peak current for achieving the targeted switching speeds for the targeted power MOSFET.

Using the example of a power MOSFET, the system requirement for the switching speed is typically described in terms of the slew rate of the drain-to-source voltage of the power MOSFET (such as dV_{DS}/dt). For example, the system requirement might state that a SPP20N60C3 power MOSFET must be turned on with a dV_{DS}/dt of 20 V/ns or higher under a DC bus voltage of 400 V in a continuous-conduction-mode (CCM) boost PFC-converter application. This type of application is an inductive hard-switching application and reducing switching power losses is critical. This requirement means that the entire drain-to-source voltage swing during power MOSFET turnon event (from 400 V in the OFF state to $V_{DS(on)}$ in on state) must be completed in approximately 20 ns or less. When the drain-to-source voltage swing occurs, the Miller charge of the power MOSFET (QGD parameter in SPP20N60C3 power MOSFET data sheet = 33 nC typical) is supplied by the peak current of gate driver. According to power MOSFET inductive switching mechanism, the gate-to-source voltage of the power MOSFET at this time is the Miller plateau voltage, which is typically a few volts higher than the threshold voltage of the power MOSFET, $V_{GS(TH)}$.

To achieve the targeted dV_{DS}/dt , the gate driver must be capable of providing the QGD charge in 20 ns or less. In other words a peak current of 1.65 A ($= 33\text{ nC} / 20\text{ ns}$) or higher must be provided by the gate driver. The UCC27532-Q1 series of gate drivers can provide 2.5-A peak sourcing current, and 5A peak sinking current which clearly exceeds the design requirement and has the capability to meet the switching speed needed. The 1.5x sourcing, and 3x sinking overdrive capability provides an extra margin against part-to-part variations in the QGD parameter of the power MOSFET along with additional flexibility to insert external gate resistors and fine tune the switching speed for efficiency versus EMI optimizations. However, in practical designs the parasitic trace inductance in the gate drive circuit of the PCB will have a definitive role to play on the power MOSFET switching speed. The effect of this trace inductance is to limit the dI/dt of the output current pulse of the gate driver. To illustrate this, consider output current pulse waveform from the gate driver to be approximated to a triangular profile, where the area under the triangle ($\frac{1}{2} \times I_{PEAK} \times \text{time}$) would equal the total gate charge of the power MOSFET (QG parameter in SPP20N60C3 power MOSFET data sheet = 87 nC typical). If the parasitic trace inductance limits the dI/dt then a situation may occur in which the full peak current capability of the gate driver is not fully achieved in the time required to deliver the QG required for the power MOSFET switching. In other words, the time parameter in the equation would dominate and the I_{PEAK} value of the current pulse would be much less than the true peak current capability of the device, while the required QG is still delivered. Because of this, the desired switching speed may not be realized, even when theoretical calculations indicate the gate driver can achieve the targeted switching speed. Thus, placing the gate driver device very close to the power

MOSFET and designing a tight gate drive-loop with minimal PCB trace inductance is important to realize the full peak-current capability of the gate driver.

8.2.1.2.5 Enable and Disable Function

Certain applications demand independent control of the output state of the driver without involving the input signal. A pin which offers an enable and disable function achieves this requirement.

8.2.1.2.6 Propagation Delay

The acceptable propagation delay from the gate driver is dependent on the switching frequency at which it is used and the acceptable level of pulse distortion to the system. See [节 6.6](#) for the propagation and switching characteristics of the UCC27532-Q1 devices.

8.2.1.2.7 Power Dissipation

Power dissipation of the gate driver has two portions as shown in equation below:

$$P_{DISS} = P_{DC} + P_{SW} \quad (1)$$

The DC portion of the power dissipation is $P_{DC} = I_Q \times V_{DD}$ where I_Q is the quiescent current for the driver. The quiescent current is the current consumed by the device to bias all internal circuits such as input stage, reference voltage, logic circuits, protections etc and also any current associated with switching of internal devices when the driver output changes state (such as charging and discharging of parasitic capacitances, parasitic shoot-through). The UCC27532-Q1 features very low quiescent currents (less than 1 mA) and contains internal logic to eliminate any shoot-through in the output driver stage. Thus the effect of the P_{DC} on the total power dissipation within the gate driver can be safely assumed to be negligible. In practice this is the power consumed by driver when its output is disconnected from the gate of power switch.

The power dissipated in the gate driver package during switching (P_{SW}) depends on the following factors:

- Gate charge required of the power device (usually a function of the drive voltage V_G , which is very close to input bias supply voltage V_{DD} due to low V_{OH} drop-out)
- Switching frequency
- Use of external gate resistors

When a driver device is tested with a discrete, capacitive load it is a fairly simple matter to calculate the power that is required from the bias supply. The energy that must be transferred from the bias supply to charge the capacitor is given by:

$$E_G = \frac{1}{2} C_{LOAD} V_{DD}^2 \quad (2)$$

where

- C_{LOAD} is load capacitor and V_{DD} is bias voltage feeding the driver.

There is an equal amount of energy dissipated when the capacitor is discharged. During turnoff the energy stored in capacitor is fully dissipated in drive circuit. This leads to a total power loss during switching cycle given by the following:

$$P_G = C_{LOAD} V_{DD}^2 f_{sw} \quad (3)$$

where

- f_{sw} is the switching frequency

The switching load presented by a power FET and IGBT can be converted to an equivalent capacitance by examining the gate charge required to switch the device. This gate charge includes the effects of the input

capacitance plus the added charge needed to swing the drain voltage of the power device as it switches between the ON and OFF states. Most manufacturers provide specifications of typical and maximum gate charge, in nC, to switch the device under specified conditions. Using the gate charge Q_g , one can determine the power that must be dissipated when charging a capacitor. This is done by using the equivalence, $Q_g = C_{LOAD}V_{DD}$, to provide the following equation for power:

$$P_G = C_{LOAD}V_{DD}^2f_{sw} = Q_gV_{DD}f_{sw} \tag{4}$$

This power P_G is dissipated in the resistive elements of the circuit when the MOSFET and IGBT is being turned on or off. Half of the total power is dissipated when the load capacitor is charged during turnon, and the other half is dissipated when the load capacitor is discharged during turnoff. When no external gate resistor is employed between the driver and MOSFET and IGBT, this power is completely dissipated inside the driver package. With the use of external gate drive resistors, the power dissipation is shared between the internal resistance of driver and external gate resistor in accordance to the ratio of the resistances (more power dissipated in the higher resistance component). Based on this simplified analysis, the driver power dissipation during switching is calculated as follows:

$$P_{SW} = 0.5 \times Q_g \times V_{DD} \times f_{sw} \left(\frac{R_{OFF}}{(R_{OFF} + R_{GATE})} + \frac{R_{ON}}{(R_{ON} + R_{GATE})} \right) \tag{5}$$

where

- $R_{OFF} = R_{OL}$ and R_{ON} (effective resistance of pullup structure) = 3 x R_{OL}

8.2.1.3 Application Curves

The following application curves were observed using the UCC27531 on the UCC27531EVM-184.

备注

Legend: Green: EVM PWM Input, Blue: UCC27531 IN, Red: EVM GATE Output

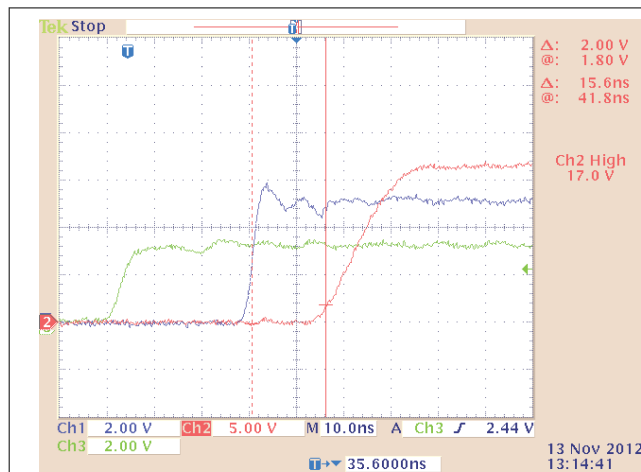


图 8-2. UCC27531DBV Input vs Output PWM Propagation Delay (high)

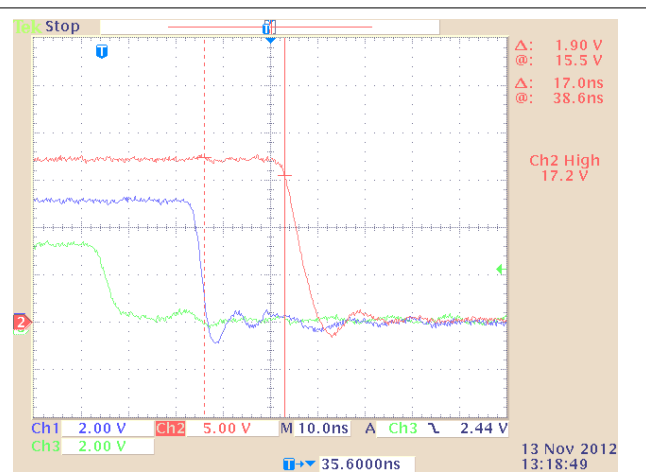


图 8-3. UCC27531DBV Input vs Output PWM Propagation Delay (low)

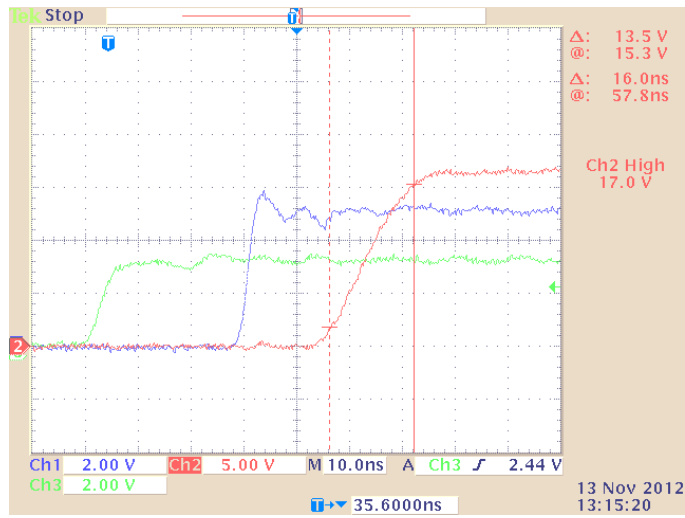


图 8-4. UCC27531DBV Input vs Output PWM Rise Time

8.2.2 Driving IGBT With 13-V Negative Turnoff Bias

The circuit configuration in 图 8-5 includes an additional 13-V supply, which is configured to bias the gate of the IGBT at 13-V negative with respect to its emitter. The negative voltage on the gate terminal ensures safe turn off of the IGBT and ensures that the IGBT remains in the blocking state in the presence of high dv/dt voltages on the collector terminal.

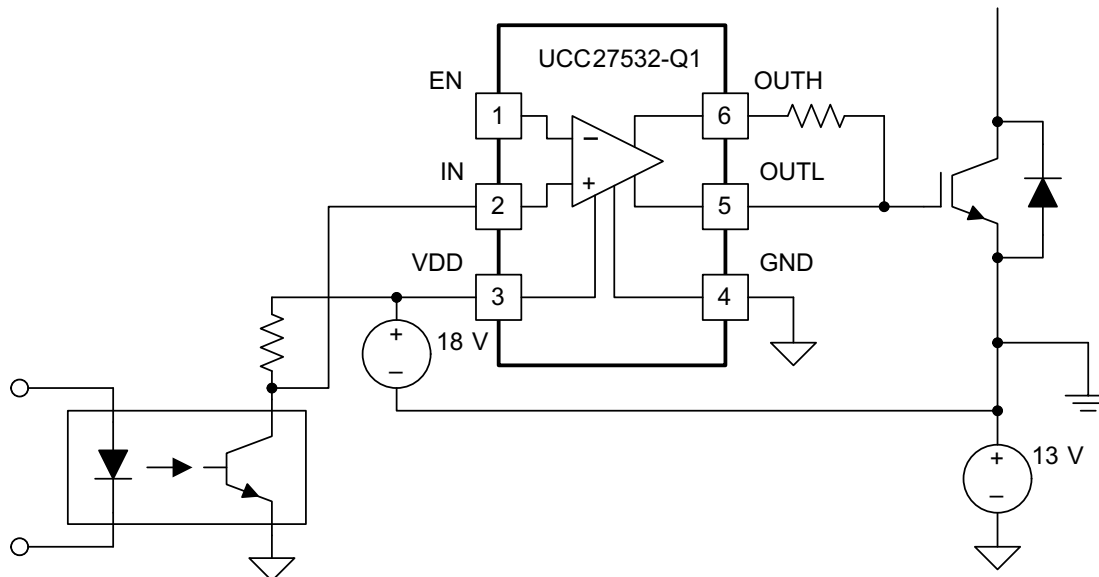


图 8-5. Driving IGBT With 13-V Negative Turnoff Bias Schematic

8.2.3 Using UCC27532-Q1 Drivers in an Inverter

In the inverter circuit shown in 图 8-6, the UCC27532-Q1 drivers for the IGBTs will require the drivers to be supplied by individually isolated power supplies to enable them to drive the floating IGBT devices in the power stage.

In addition the gate drive signals from the micro-controller to the UCC27532-Q1 will also must level shifted through isolation devices.

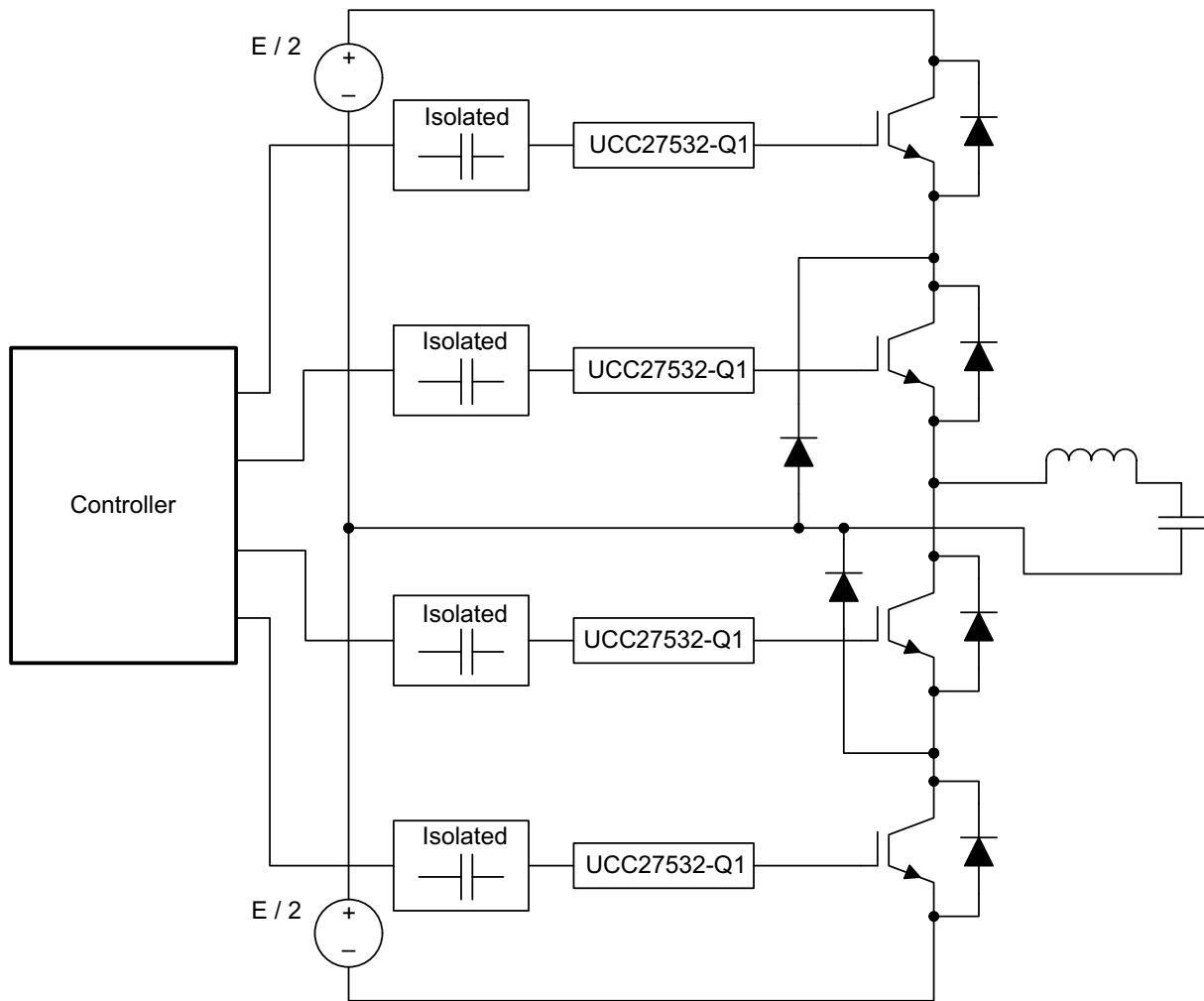


图 8-6. Using UCC27532-Q1 Drivers in an Inverter

9 Power Supply Recommendations

The bias supply voltage range for which the UCC27532-Q1 devices are rated to operate is from 10 V to 32 V. The lower end of this range is governed by the internal UVLO protection feature on the VDD pin supply circuit blocks. Whenever the driver is in UVLO condition when the VDD pin voltage is below the V(ON) supply start threshold, this feature holds the output low, regardless of the status of the inputs. The upper end of this range is driven by the 35-V absolute maximum voltage rating of the VDD pin of the device (which is a stress rating). Keeping a 3-V margin to allow for transient voltage spikes, the maximum recommended voltage for the VDD pin is 32 V.

The UVLO protection feature also involves a hysteresis function. This means that when the VDD pin bias voltage has exceeded the threshold voltage and device begins to operate, and if the voltage drops, then the device continues to deliver normal functionality unless the voltage drop exceeds the hysteresis specification VDD(hys). Therefore, ensuring that, while operating at or near the 9.8 V range, the voltage ripple on the auxiliary power supply output is smaller than the hysteresis specification of the device is important to avoid triggering device shutdown.

During system shutdown, the device operation continues until the VDD pin voltage has dropped below the V(OFF) threshold which must be accounted for while evaluating system shutdown timing design requirements. Likewise, at system start-up, the device does not begin operation until the VDD pin voltage has exceeded above the V(ON) threshold. The quiescent current consumed by the internal circuit blocks of the device is supplied through the VDD pin. Although this fact is well known, recognizing that the charge for source current pulses delivered by the OUT pin is also supplied through the same VDD pin is important. As a result, every time a current is sourced out of the output pin (OUT), a corresponding current pulse is delivered into the device through the VDD pin. Thus ensuring that local bypass capacitors are provided between the VDD and GND pins and located as close to the device as possible for the purpose of decoupling is important. A low-ESR, ceramic surface-mount capacitor is mandatory.

10 Layout

10.1 Layout Guidelines

Proper PCB layout is extremely important in a high-current fast-switching circuit to provide appropriate device operation and design robustness. The UCC27532-Q1 gate driver incorporates short propagation delays and powerful output stages capable of delivering large current peaks with very fast rise and fall times at the gate of power switch to facilitate voltage transitions very quickly. At higher VDD voltages, the peak current capability is even higher (2.5-A and 5-A peak current is at VDD = 18 V). Very high di/dt can cause unacceptable ringing if the trace lengths and impedances are not well controlled. TI strongly recommends adhering to the following circuit layout guidelines when designing with these high-speed drivers.

- Locate the driver device as close as possible to the power device to minimize the length of high-current traces between the driver output pins and the gate of the power-switch device.
- Locate the VDD bypass capacitors between VDD and GND as close as possible to the driver with minimal trace length to improve the noise filtering. These capacitors support high peak current being drawn from VDD during turnon of power switch. TI highly recommends using low-inductance SMD components such as chip resistors and chip capacitors.
- The turnon and turnoff current-loop paths (driver device, power switch, and VDD bypass capacitor) must be minimized as much as possible to keep the stray inductance to a minimum. High di/dt is established in these loops at two instances — during turnon and turnoff transients — which induces significant voltage transients on the output pins of the driver device and gate of the power switch.
- Wherever possible, parallel the source and return traces of a current loop which takes advantage of flux cancellation
- Separate power traces and signal traces, such as output and input signals.
- Star-point grounding is a good way to minimize noise coupling from one current loop to another. The GND of the driver must be connected to the other circuit nodes such as source of power switch, ground of PWM controller, and others at one, single point. The connected paths must be as short as possible to reduce inductance and be as wide as possible to reduce resistance.
- Use a ground plane to provide noise shielding. Fast rise and fall times at OUT can corrupt the input signals during transition. The ground plane must not be a conduction path for any current loop. Instead the ground plane must be connected to the star-point with one single trace to establish the ground potential. In addition to noise shielding, the ground plane can help in power dissipation as well.

10.2 Layout Example

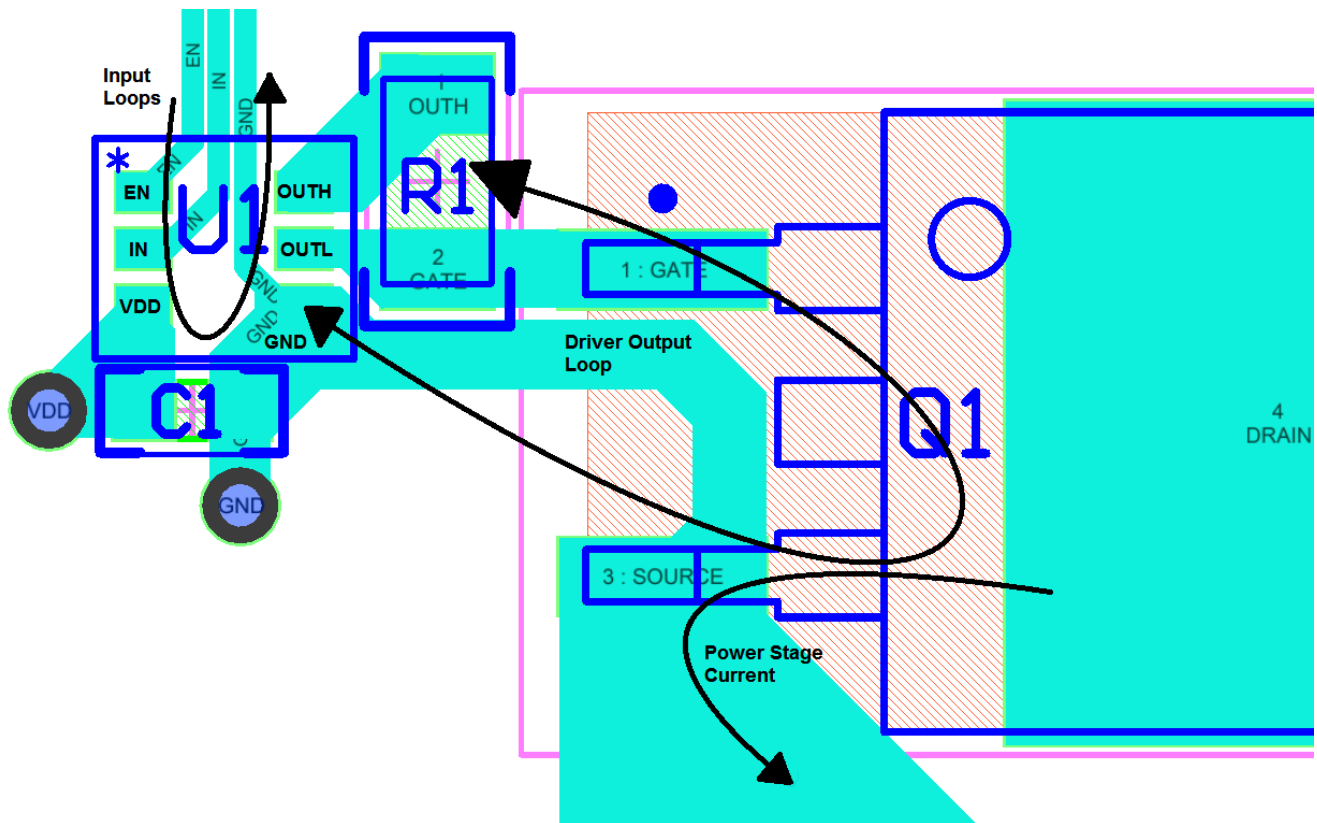


图 10-1. Layout Example: UCC27531DBV

10.3 Thermal Consideration

The useful range of a driver is greatly affected by the drive power requirements of the load and the thermal characteristics of the package. In order for a gate driver to be useful over a particular temperature range the package must allow for the efficient removal of the heat produced while keeping the junction temperature within rated limits. The thermal metrics for the driver package is summarized in the [节 6.4](#) table. For detailed information regarding the thermal information table, see [SPRA953](#).

11 Device and Documentation Support

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11.2 Documentation Support

11.2.1 Related Documentation

For related documentation see the following:

- *Using the UCC27531EVM-184*, [SLUUA70](#)
- *UCC27531-Q1 2.5-A and 5-A, 35-VMAX VDD FET and IGBT Single-Gate Driver*, [SLVSC82](#)

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

12 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (August 2015) to Revision C (September 2024) Page

- 从“特性”中删除了 HBM 和 CDM ESD 分类等级..... 1
- 更新了应用链接..... 1
- Added VDD = 16V to *INPUT (IN)* and *ENABLE (EN)* test conditions..... 6

Changes from Revision A (January 2014) to Revision B (August 2015) Page

- 添加了 ESD 等级表、特性说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分..... 1

Changes from Revision * (December 2013) to Revision A (January 2014) Page

- 将文档状态从产品预发布更改为量产数据..... 3

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
UCC27532QDBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 140	EAIQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF UCC27532-Q1 :

- Catalog : [UCC27532](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
UCC27532QDBVRQ1	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
UCC27532QDBVRQ1	SOT-23	DBV	6	3000	180.0	180.0	18.0



DBV0006A

PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



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NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
- Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Reference JEDEC MO-178.

EXAMPLE BOARD LAYOUT

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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